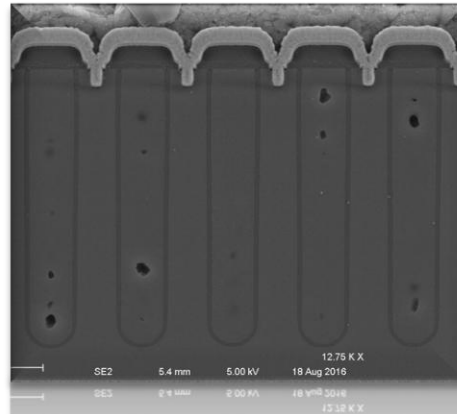


# IKW40N65H5A

Infineon 650V High Speed 5 IGBT in TRENCHSTOP™5 Technology



## Product Analysis Report

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To Know



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